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(54) Title of the Invention:

 Method of forming contact hole

Abstract:

The present invention relates to a method of forming a contact hole of a semiconductor device including forming a predetermine metal layer pattern 12. In particular, the method includes forming a first dielectric layer 13 on a predetermined structure, forming a spin-on-glass (SOG) layer 14 on the structure, implanting predetermined ions into the SOG layer 14 in order to suppress emission of OH radicals and performing a first curing process, forming a first curing process, forming a second dielectric layer 15 on the SOG layer 14, and removing the second dielectric layer 15, the SOG layer 14, and the first dielectric layer 13 in a predetermined region. Accordingly, it is possible to prevent OH radicals from discharging from the SOG layer 14 and thus prevent holes or a naturally oxidized layer from forming between metal layers. Furthermore, it is possible to enhance semiconductor device yields and reliability.